Please amend the claims as follows:

Claim 1. (Currently Amended).

A process for the wet chemical treatment of semiconductor wafers with treatment liquids in baths, ~~comprising~~ consisting of the steps of

firstly treating the semiconductor wafers in a bath with an aqueous HF solution ~~only~~ containing HF and optionally HCl and optionally a surfactant;

then treating the semiconductor wafers in a bath with an aqueous O_3 solution ~~only~~ containing O_3 and optionally HF; and

then treating the semiconductor wafers in a bath with an aqueous HCl solution ~~only~~ containing HCl and optionally O_3;

whereby these treatment steps form a treatment sequence B_2, which avoids rinsing with water or another treatment liquid and the addition of fresh water or other liquids to the treatment baths.

Claim 2. (Previously Presented).

The process as claimed in claim 1,

wherein the treatment sequence B_2 is preceded by a treatment

B_1 of the semiconductor wafers with an aqueous SC-1 solution.

Claim 3. (Original). [4]

The process as claimed in claim 1,

wherein the treatment sequence B_2 is followed by a treatment

B_3 comprising drying the semiconductor wafers.

Claim 4. (Original). [5]

The process as claimed in claim 3, [4]

wherein the treatment of the semiconductor wafers is

sequenced according to the term $m* (B_1 + B_2) + B_3$,

m being an integer number and the treatment B_1 and the

treatment sequence B_2 being carried out in succession, and

this taking place m times, before the drying treatment B_3 is

performed.

Claim 5. (Original). [7]

The process as claimed claim 1,

wherein in treatment sequence B_2, the aqueous HF solution

contains HF in a concentration of from 0.001% to 2% by weight and

optionally HCl in a concentration of up to 2% by weight and

optionally a surfactant; and

wherein all percents by weight are based upon the total

solution weight.

Claim 9. (Original).

The process as claimed in claim 1,

wherein in treatment sequence B_2, the aqueous O_3 solution

contains O_3 in a concentration of from 1 ppm to 30 ppm and is

optionally exposed to megasonic waves.

Claim 7. (Original).

The process as claimed in claim 1,

wherein the treatment liquid used last in the treatment

sequence B_2 contains ozone and is optionally exposed to megasonic

waves.

Claim 6. (Original).

The process as claimed in claim 3,

wherein the drying treatment is carried out using a step

selected from the group consisting of centrifuging, using hot

water, using isopropanol, and using marangoni principle.

Claim ~~9~~ 3 (Previously Presented).

The process as claimed in claim 2,

wherein in treatment B_1 the aqueous SC-1 solution contains a liquid selected from the group consisting of NH_4OH and H_2O_2, and TMAH (= tetramethylammonium hydroxide) and H_2O_2.

Claim 10 (Cancelled).

Claim ~~11~~ 10 (Currently Amended).

A process for the wet chemical treatment of semiconductor wafers with treatment liquids in baths, ~~comprising~~ consisting of the steps of

firstly treating the semiconductor wafers in a bath with an aqueous HF solution ~~only~~ containing HF and optionally HCl and optionally a surfactant;

then treating the semiconductor wafers in a bath with an aqueous O_3 solution ~~only~~ containing O_3 and optionally HF; and

then treating the semiconductor wafers in a bath with an aqueous HCl solution ~~only~~ containing HCl and optionally O_3 with exposure to megasonic waves,

whereby these treatment steps form a treatment sequence B_2, which avoids rinsing with water or another treatment liquid and the addition of fresh water or other liquids to the treatment

baths.

Please add new claims 12 to 15 as follow:

Claim 12. (New).

A process for the wet chemical treatment of semiconductor wafers with treatment liquids in baths, comprising the steps of

firstly treating the semiconductor wafers in a bath with an aqueous HF solution containing HF and optionally HCl and optionally a surfactant;

then treating the semiconductor wafers in a bath with an aqueous O_3 solution containing O_3 and optionally HF; and

then treating the semiconductor wafers in a bath with an aqueous HCl solution containing HCl and optionally O_3;

whereby these treatment steps form a treatment sequence B_2; and

circulating the treatment liquids of said baths by taking a part from each of said baths, filtering and returning the part to the corresponding treatment bath.

Claim 13. (New).

A process for the wet chemical treatment of semiconductor wafers with treatment liquids in baths, comprising the steps of

firstly treating the semiconductor wafers in a bath with an aqueous HF solution containing HF and optionally HCl and optionally a surfactant;

then treating the semiconductor wafers in a bath with an aqueous O_3 solution containing O_3 and optionally HF; and

then treating the semiconductor wafers in a bath with an aqueous HCl solution containing HCl and optionally O_3 with exposure to megasonic waves;

whereby these treatment steps form a treatment sequence B_2; and

circulating the treatment liquids of said baths by taking a part from each of said baths, filtering and returning the part to the corresponding treatment bath.

Claim 14. (New).

A process for the wet chemical treatment of semiconductor wafers with treatment liquids in baths, comprising the steps of

firstly treating the semiconductor wafers in a bath with an aqueous HF solution containing HF and optionally HCl and optionally a surfactant;

then treating the semiconductor wafers in a bath with an

aqueous O$_3$ solution containing O$_3$ and optionally HF; and

then treating the semiconductor wafers in a bath with an aqueous HCl solution containing HCl and optionally O$_3$; and

circulating the treatment liquids of said baths by taking a part from each of said baths, filtering and returning the part to the corresponding treatment bath;

whereby these treatment steps form a treatment sequence B$_2$, which avoids rinsing with water or another treatment liquid and the addition of fresh water or other liquids to the treatment baths.

Claim 14. (New).

A process for the wet chemical treatment of semiconductor wafers with treatment liquids in baths, comprising the steps of

firstly treating the semiconductor wafers in a bath with an aqueous HF solution containing HF and optionally HCl and optionally a surfactant;

then treating the semiconductor wafers in a bath with an aqueous O$_3$ solution containing O$_3$ and optionally HF; and

then treating the semiconductor wafers in a bath with an aqueous HCl solution containing HCl and optionally O$_3$ with exposure to megasonic waves; and

circulating the treatment liquids of said baths by taking a

part from each of said baths, filtering and returning the part to the corresponding treatment bath;

whereby these treatment steps form a treatment sequence B_2, which avoids rinsing with water or another treatment liquid and the addition of fresh water or other liquids to the treatment baths.